

March 1999

## FDC6323L Integrated Load Switch

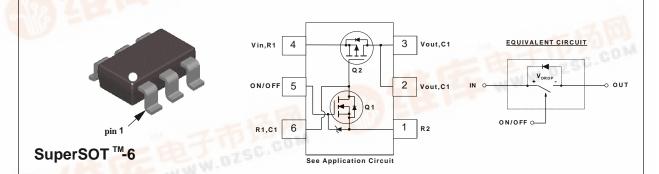
#### **General Description**

These Integrated Load Switches are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage high side load switch application where low conduction loss and ease of driving are needed.

#### **Features**

- High density cell design for extremely low on-resistance.
- V<sub>ON/OFF</sub> Zener protection for ESD ruggedness. >6KV Human Body Model.
- SuperSOT<sup>™</sup>-6 package design using copper lead frame for superior thermal and electrical capabilities.





Absolute Maximum Ratings T. = 25°C unless otherwise noted

Symbol	Parameter	FDC6323L	Units
V <sub>IN</sub>	Input Voltage Range	3-8	V
V <sub>ON/OFF</sub>	On/Off Voltage Range	1.5 - 8	V
I <sub>L</sub>	Load Current @ V <sub>DROP</sub> =0.5V - Continuous (Note 1)	1.5	Α
	- Pulsed (Note 1 & 3)	2.5	
P <sub>D</sub>	Maximum Power Dissipation (Note 2a)	0.7	W
T <sub>J</sub> ,T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf/1500Ohm)	6	kV
THERMA	L CHARACTERISTICS		
R <sub>eJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 2a)	180	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	60	°C/W

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHA	RACTERISTICS					
I <sub>FL</sub>	Forward Leakage Current	$V_{IN} = 8 \text{ V}, V_{ONOFF} = 0 \text{ V}$			1	μΑ
I <sub>RL</sub>	Reverse Leakage Current	$V_{IN} = -8 \text{ V}, V_{ON/OFF} = 0 \text{ V}$			-1	μΑ
ON CHAR	ACTERISTICS (Note 3)					
V <sub>IN</sub>	Input Voltage		3		8	V
V <sub>ON/OFF</sub>	On/Off Voltage		1.5		8	V
$V_{DROP}$	Conduction Voltage Drop @ 1A	$V_{IN} = 5 \text{ V}, \ V_{ON/OFF} = 3.3 \text{ V}$		0.145	0.2	V
		$V_{IN} = 3.3 \text{ V}, \ V_{ON/OFF} = 3.3 \text{ V}$		0.178	0.3	
I <sub>L</sub>	Load Current	$V_{DROP} = 0.2 \text{ V}, V_{IN} = 5 \text{ V}, V_{ONOFF} = 3.3 \text{ V}$	1			Α
		$V_{DROP} = 0.3 \text{ V}, V_{IN} = 3.3 \text{ V}, V_{ONOFF} = 3.3 \text{ V}$	1			

#### Notes:

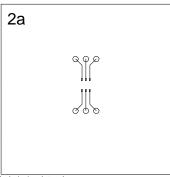
1.  $V_{IN}$ =8V,  $V_{ON/OFF}$ =8V,  $V_{DROP}$ =0.5V,  $T_A$ =25°C

2.  $R_{g,k}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{g,k}$  is guaranteed by design while  $R_{g,k}$  is determined by the user's board design.

$$P_D(t) = \frac{T_J - T_A}{R_{\text{RJ},d}(t)} = \frac{T_J - T_A}{R_{\text{RJ},d} + R_{\text{RCA}}(t)} = I_D^2(t) \times R_{\text{DS}(ON)@T_J}$$

Typical  $R_{\theta^{JA}}$  for single device operation using the board layouts shown below on FR-4 PCB in a still air environment:

a. 180°C/W when mounted on a 2oz minimum copper pad.



Scale 1 : 1 on letter size paper

3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2.0%

## Typical Electrical Characteristics ( $T_A = 25$ $^{\circ}C$ unless otherwise noted )

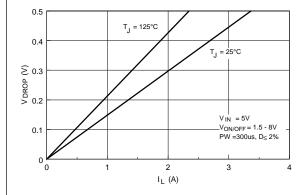
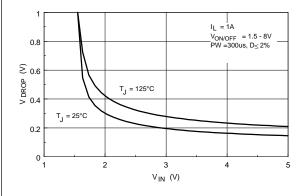


Figure 1.  $V_{DROP}$  Versus  $I_L$  at  $V_{IN} = 5V$ .

Figure 2.  $V_{DROP}$  Versus  $I_{L}$  at  $V_{IN} = 3.3V$ .



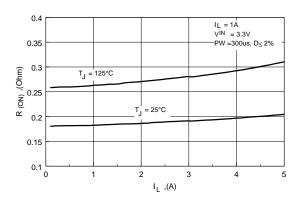


Figure 3.  $V_{DROP}$  Versus  $V_{IN}$  at  $I_L = 1A$ .

Figure 4.  $R_{(ON)}$  Versus  $I_L$  at  $V_{IN} = 3.3V$ .

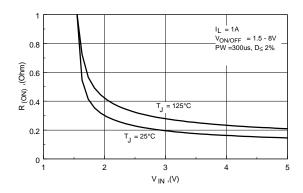
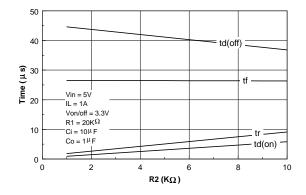


Figure 5. On Resistance Variation with Input Voltage.

## Typical Electrical Characteristics ( $T_A = 25$ $^{\circ}$ C unless otherwise noted )



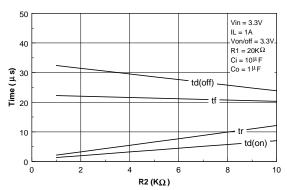
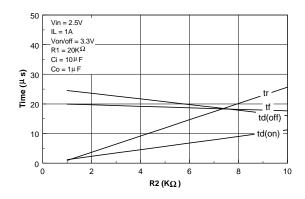


Figure 6. Switching Variation with R2 at Vin = 5V and R1 = 20KOhm.

Figure 7. Switching Variation with R2 at Vin = 3.3V and R1 = 20KOhm.



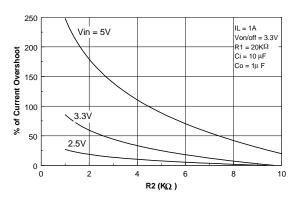
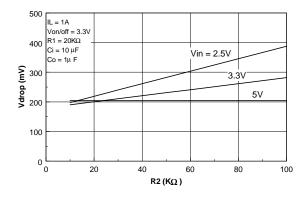


Figure 8. Switching Variation with R2 at Vin = 2.5V and R1 = 20KOhm.

Figure 9. % of Current Overshoot Variation with Vin and R2.



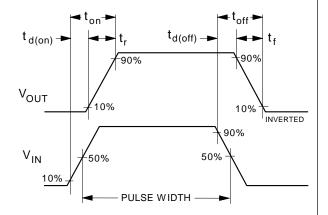


Figure 10. Vdrop Variation with Vin and R2.

Figure 11. Switching Waveforms.

## Typical Electrical Characteristics ( $T_A = 25$ $^{\circ}C$ unless otherwise noted )

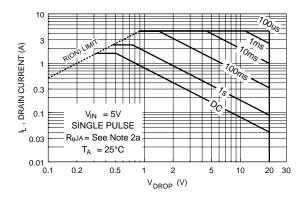


Figure 12. Safe Operating Area.

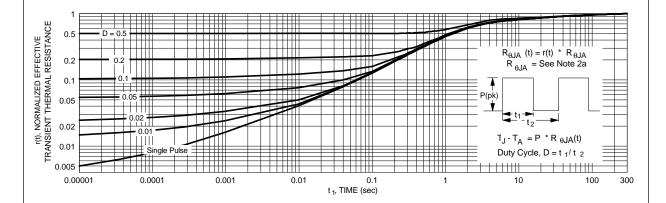
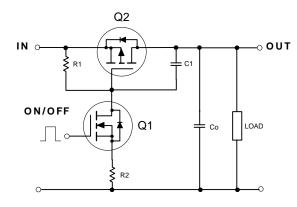


Figure 13. Transient Thermal Response Curve.

Note: Thermal characterization performed on the conditions described in Note 2a. Transient thermal response will change depends on the circuit board design.

## FDC6323L Load Switch Application

#### **APPLICATION CIRCUIT**



### **General Description**

This device is particularly suited for compact computer peripheral switching applications where 8V input and 1A output current capability are needed. This load switch integrates a small N-Channel Power MOSFET (Q1) which drives a large P-Channel Power MOSFET (Q2) in one tiny SuperSOT<sup>TM</sup>-6 package.

A load switch is usually configured for high side switching so that the load can be isolated from the active power source. A P-Channel Power MOSFET, because it does not require its drive voltage above the input voltage, is usually more cost effective than using an N-Channel device in this particular application. A large P-Channel Power MOSFET minimizes voltage drop. By using a small N-Channel device the driving stage is simplified.

## **Component Values**

R1 Typical  $10k - 1M\Omega$ 

R2 Typical 0 - 100kΩ (optional) C1 Typical 1000pF (optional)

#### **Design Notes**

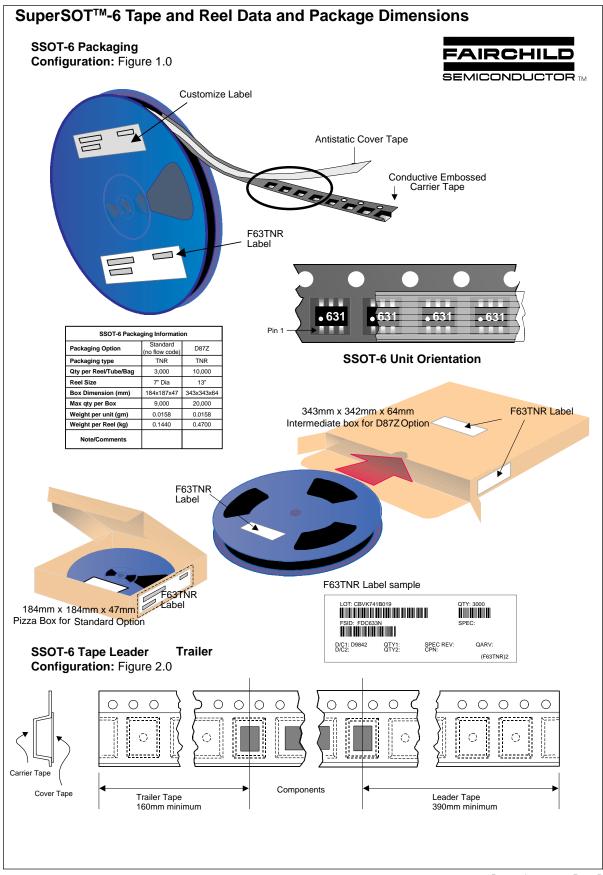
- R1 is needed to turn off Q2.
- R2 can be used to soft start the switch in case the output capacitance Co is small.
- R2 should be at least 10 times smaller than R1 to guarantee Q1 turns on.
- By using R1 and R2 a certain amount of current is lost from the input. This bias current loss is given by the equation

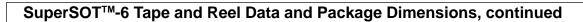
 $I_{BIAS\_LOSS} = \frac{Vin}{R1 + R2}$ 

when the switch is ON.  $I_{\mbox{\tiny BIAS LOSS}}$  can be minimized by selecting a large

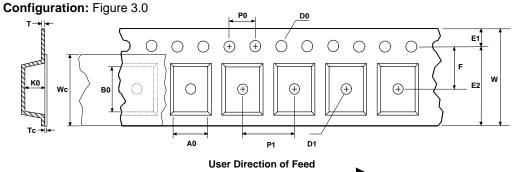
value for R1.

 R2 and C<sub>RSS</sub> of Q2 make ramp for slow turn on. If excessive overshoot current occurs due to fast turn on, additional capacitance C1 can be added externally to slow down the turn on.





## **SSOT-6 Embossed Carrier Tape**

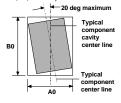


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.00 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation

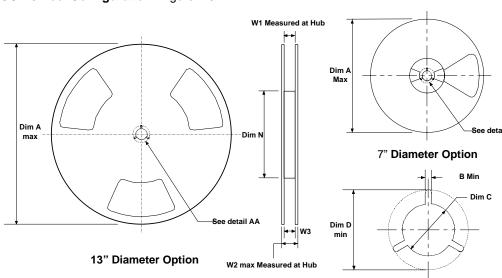


Sketch C (Top View)

Component lateral movement

DETAIL AA

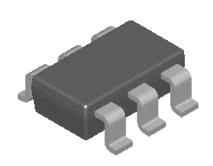
## SSOT-6 Reel Configuration: Figure 4.0

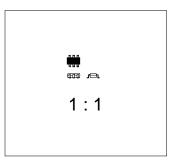


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

## SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

# SuperSOT™-6 (FS PKG Code 31, 33)

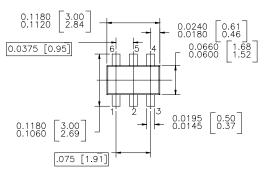


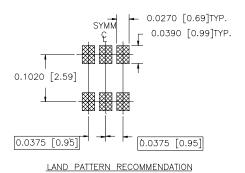


Scale 1:1 on letter size paper

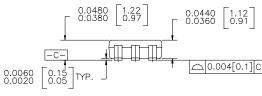
Dimensions shown below are in:
inches [millimeters]

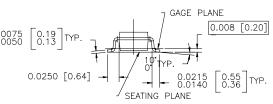
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SUPER SOT 6 LEADS

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FACT<sup>TM</sup> QS<sup>TM</sup>

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